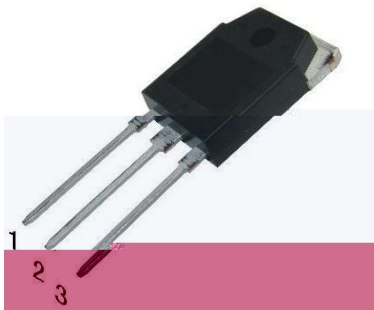
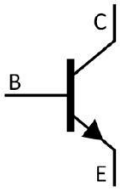


Silicon NPN transistor in a TO-3P Plastic Package.

Recommend for 200W high fidelity audio frequency amplifier output stage, Complementary to MJE21193.

Power amplifier applications.



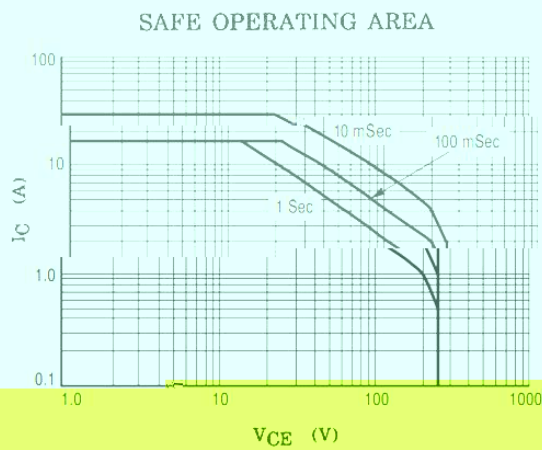
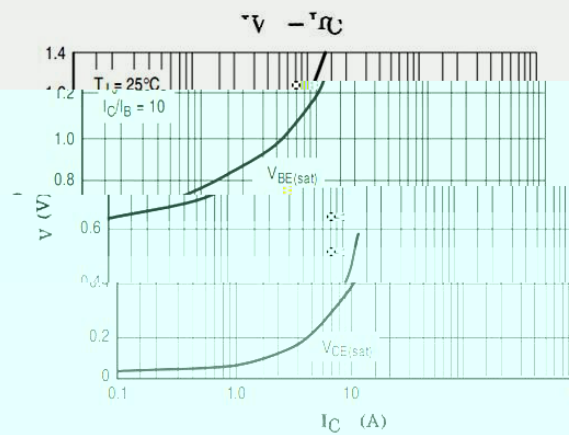
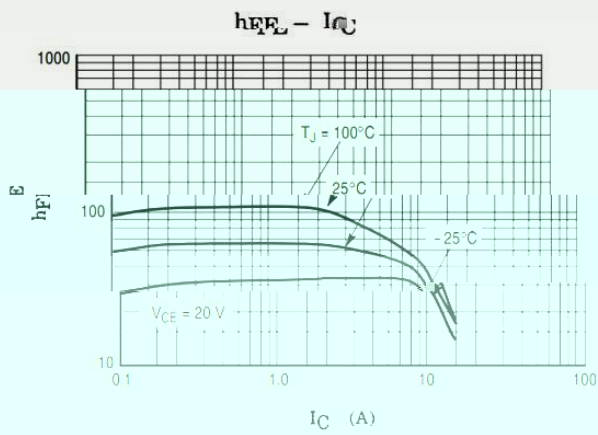
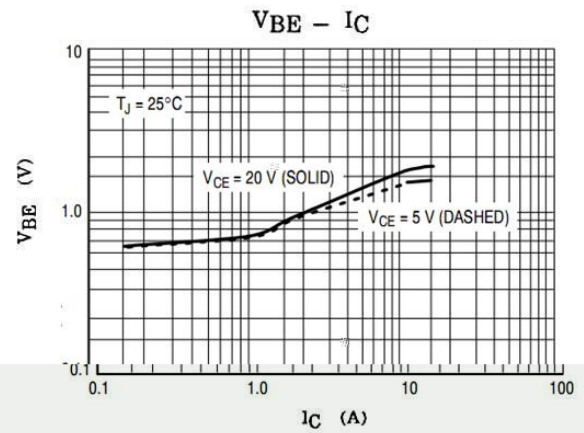
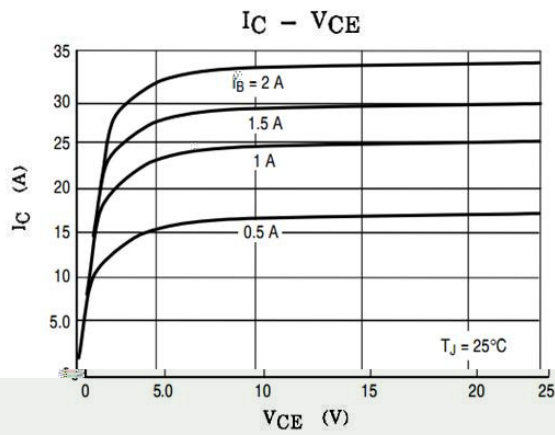
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	400	V
Collector to Emitter Voltage	V_{CEO}	250	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	16	A
Peak Collector Current	I_{CP}	30	A
Base Current	I_B	5	A
Collector Power Dissipation	$P_C(TC=25)$	200	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

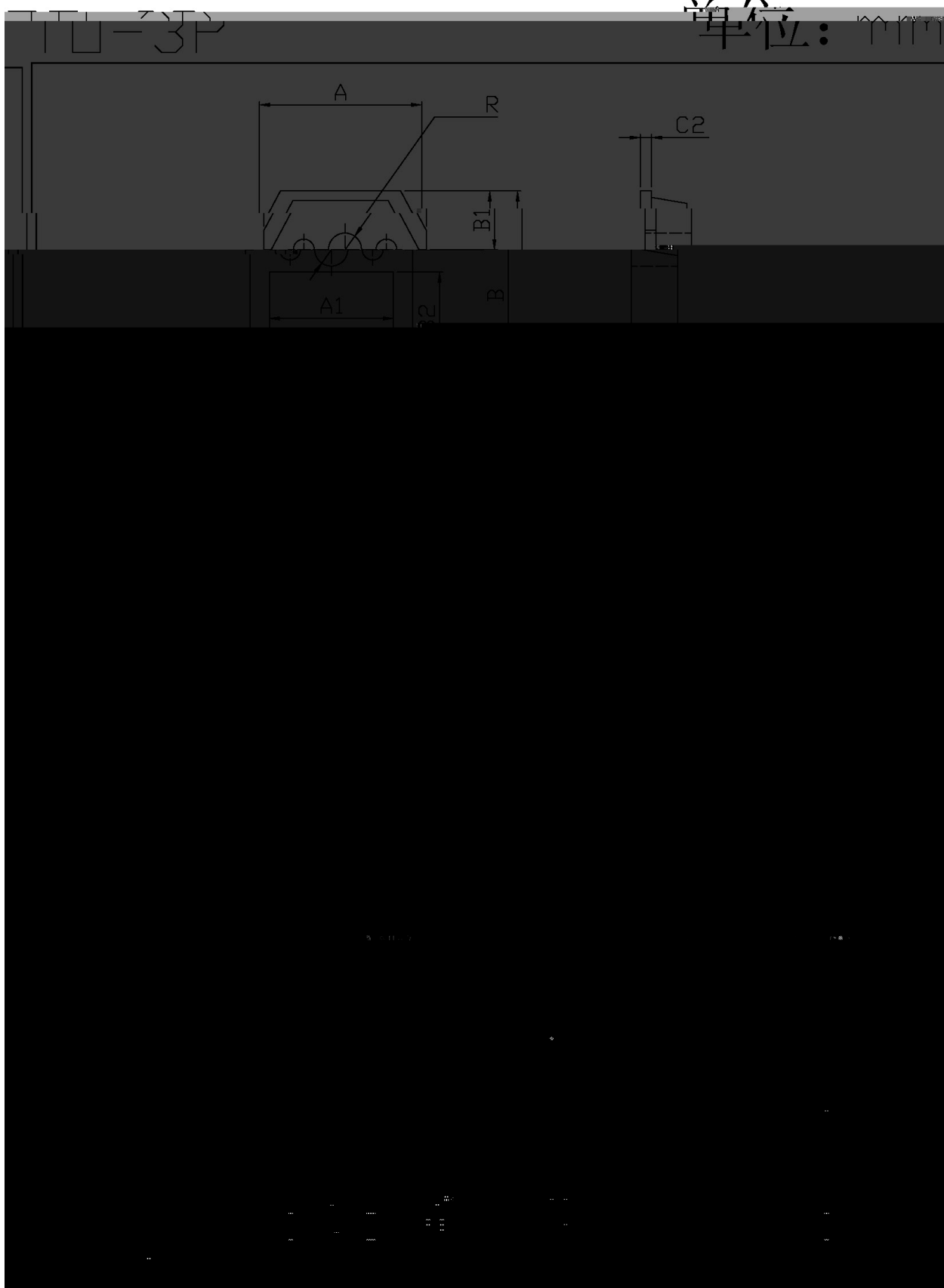
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=100mA$ $I_B=0$	250			V
Collector Cut-Off Current	I_{CEO}	$V_{CE}=200V$ $I_E=0$			100	μA
Collector Cut-Off Current	I_{CBO}	$V_{CB}=250V$ $I_E=0$			100	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			100	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5.0V$ $I_C=8.0A$	10		80	
	$h_{FE(2)}$	$V_{CE}=5.0V$ $I_C=16A$	8			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=8.0A$ $I_B=0.8A$			1.4	V
	$V_{CE(sat)(2)}$	$I_C=16A$ $I_B=3.2A$			4	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=5.0V$ $I_C=8.0A$			2.2	V
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=1.0A$ $f=1.0MHz$	4			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$			500	pF

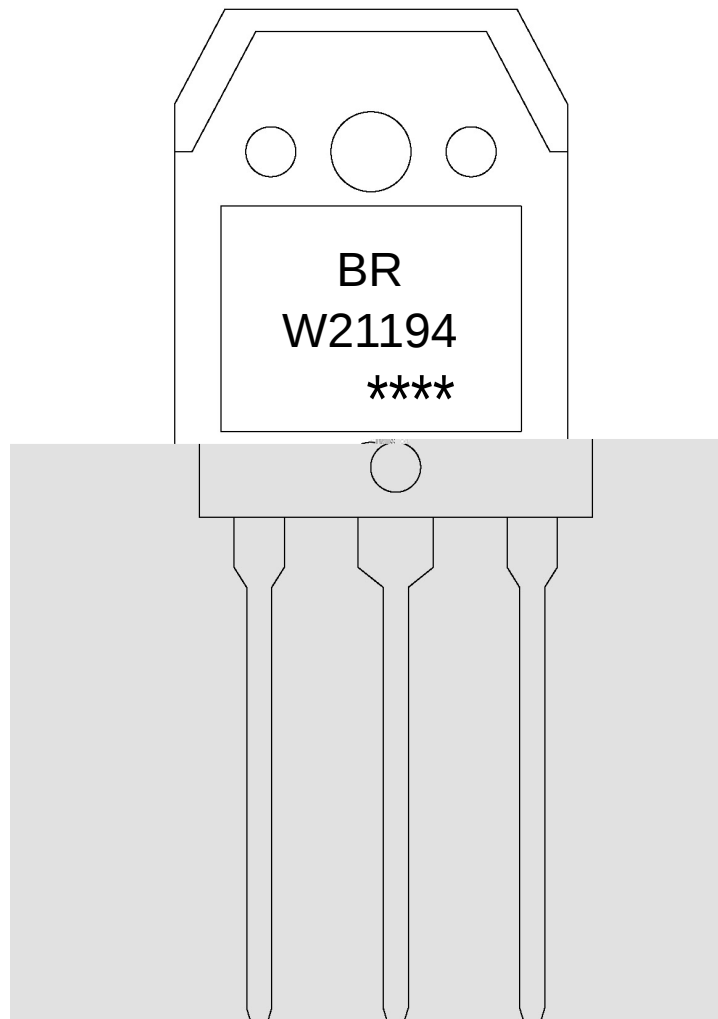
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



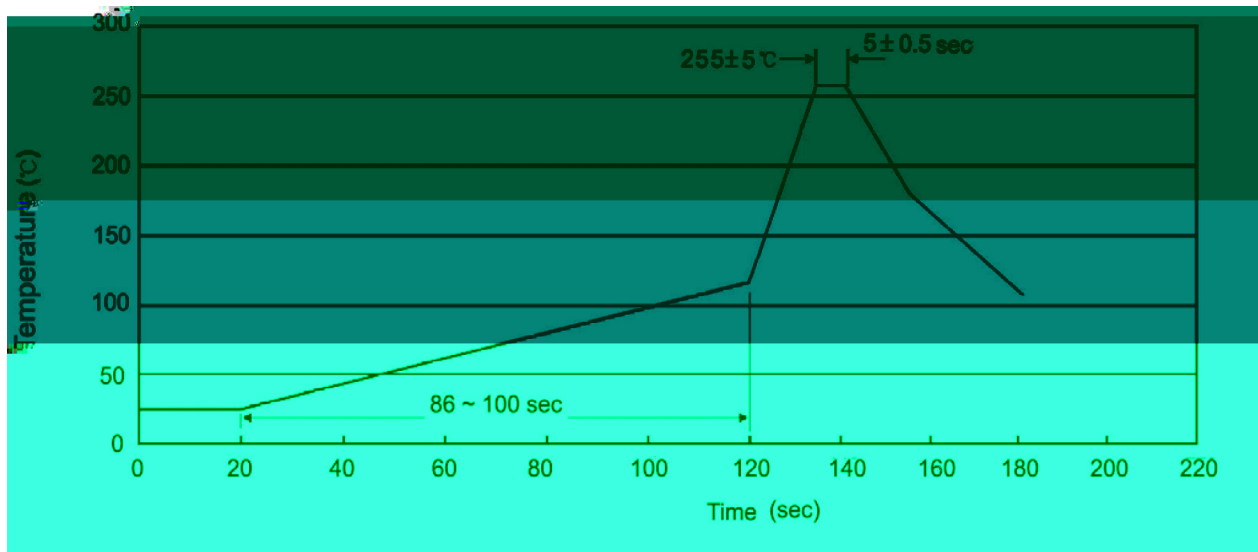
Note:

BR: Company Code.

W21194: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

1 25 150 60 90sec;

1.Preheating:25~150